

N-channel 100V 6.8 mΩ standard level MOSFET in D2PAK.

Rev. 2 — 2 March 2012

Objective data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1] -	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	269	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon} drain-source resistance	drain-source on-state	V_{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	12	mΩ
	resistance	V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	5.4	6.8	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	36	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	125	-	nC
Avalanch	e ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_{D} = 100 A; V_{sup} = 100 V; unclamped; R_{GS} = 50 Ω	-	-	315	mJ

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT404 (D2PAK)

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN7R0-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

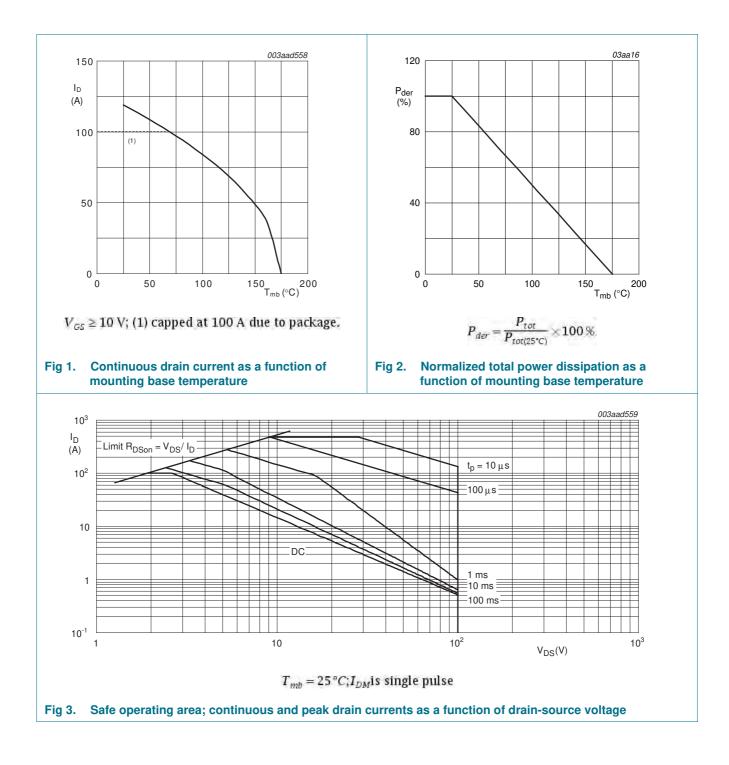
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	85	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	[1] -	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	475	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	269	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	diode				
ls	source current	T _{mb} = 25 °C	<u>[1]</u> -	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	475	А
Avalanche ru	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ I}_{D} = 100 \text{ A};$ $V_{sup} = 100 \text{ V}; \text{ unclamped}; \text{ R}_{GS} = 50 \Omega$	-	315	mJ

[1] Continuous current is limited by package.

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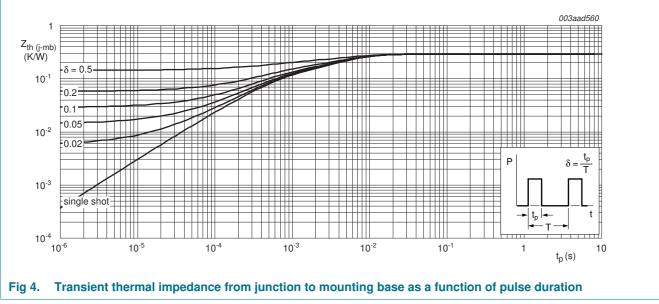
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	60	-	K/W



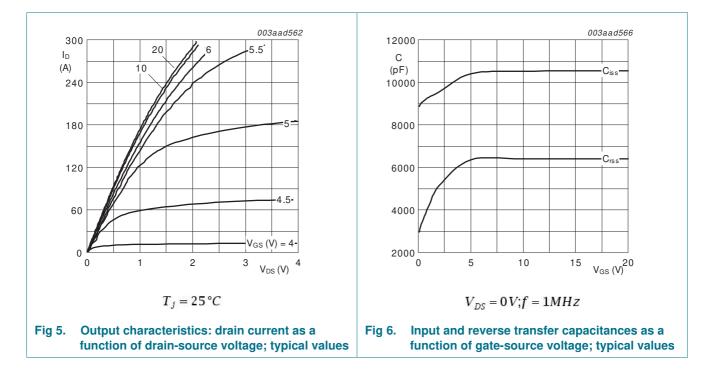
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6. Characteristics

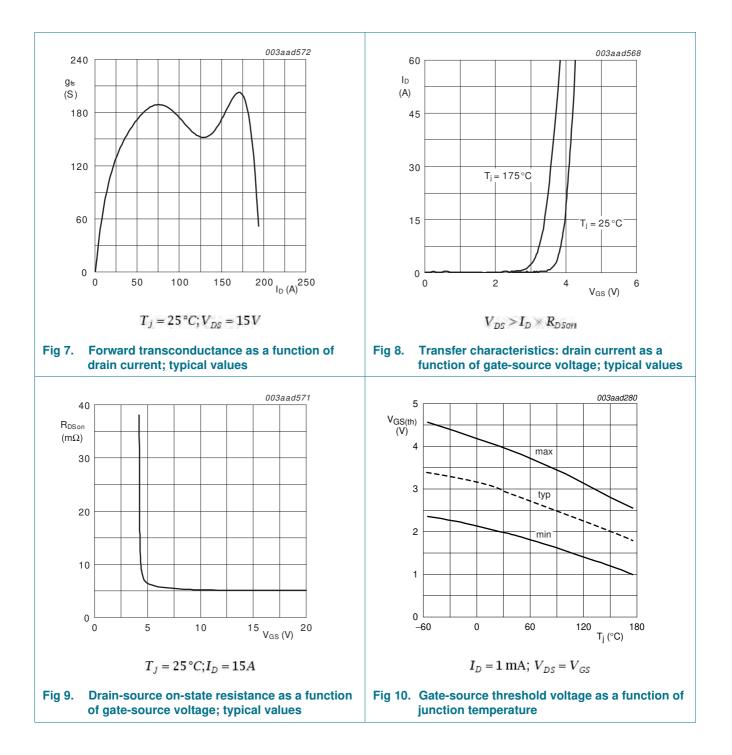
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	150	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.08	5	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	12	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	15	19	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	5.4	6.8	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.74	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	125	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	100	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15; see Figure 14	-	28	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 15</u>	-	19.4	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	9	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15; see Figure 14	-	36	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 15;</u> see <u>Figure 14</u>	-	4.3	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;	-	6686	-	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	438	-	pF
C _{rss}	reverse transfer capacitance		-	272	-	pF

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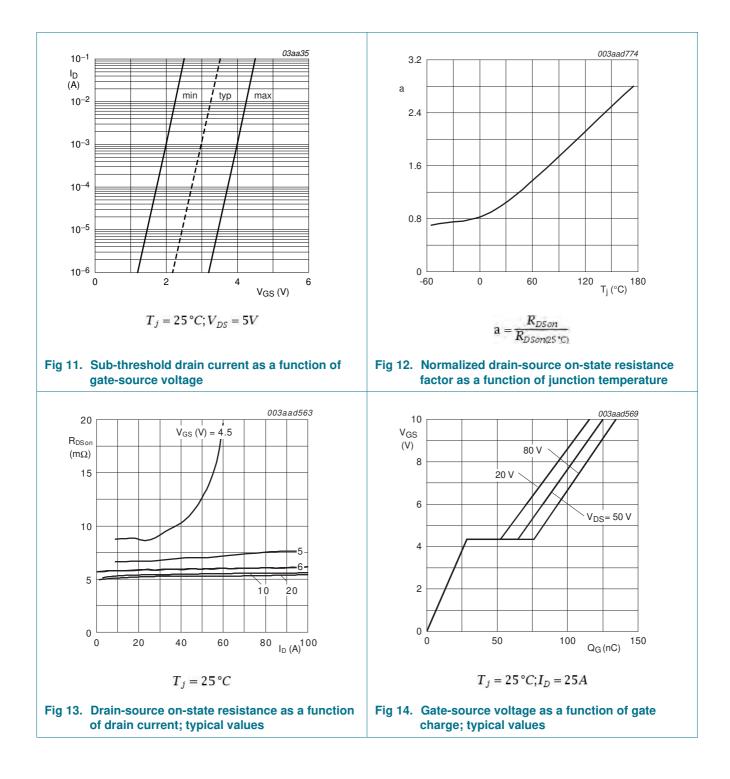
Table 6. Characteristicscontinued							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
t _{d(on)}	turn-on delay time	$V_{DS}=50~V;~R_L=2~\Omega;~V_{GS}=10~V;$	-	34.6	-	ns	
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	45.6	-	ns	
t _{d(off)}	turn-off delay time		-	103.9	-	ns	
t _f	fall time		-	49.5	-	ns	
Source-d	rain diode						
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V	
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	64	-	ns	
Q _r	recovered charge	$V_{DS} = 50 V$	-	167	-	nC	



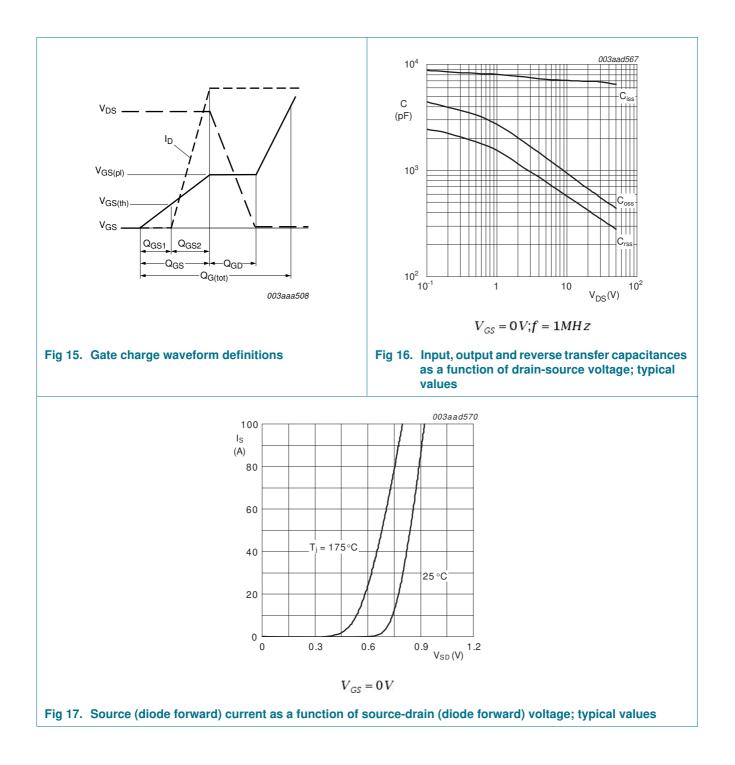
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7. Package outline

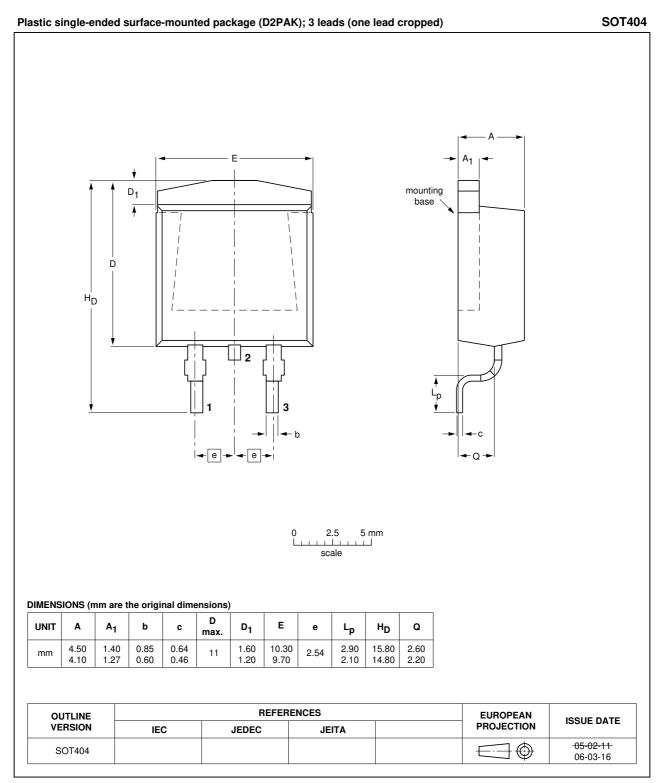


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-100BS v.2	20120302	Objective data sheet	-	PSMN7R0-100BS v.1
Modifications:	 Various changes to 	o content.		
PSMN7R0-100BS v.1	20111025	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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